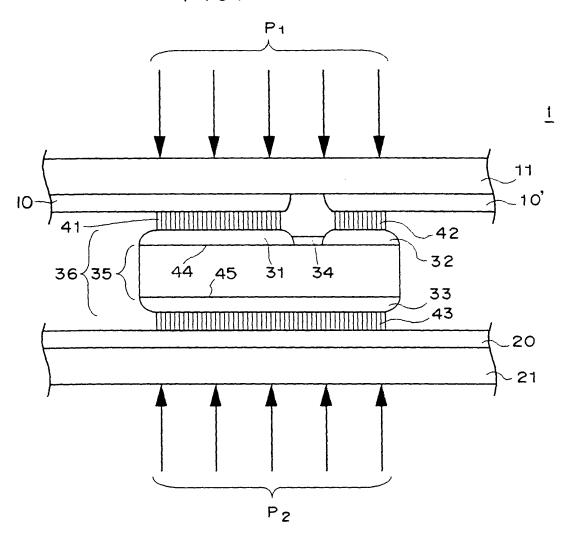
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FIG.I



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F I G . 2

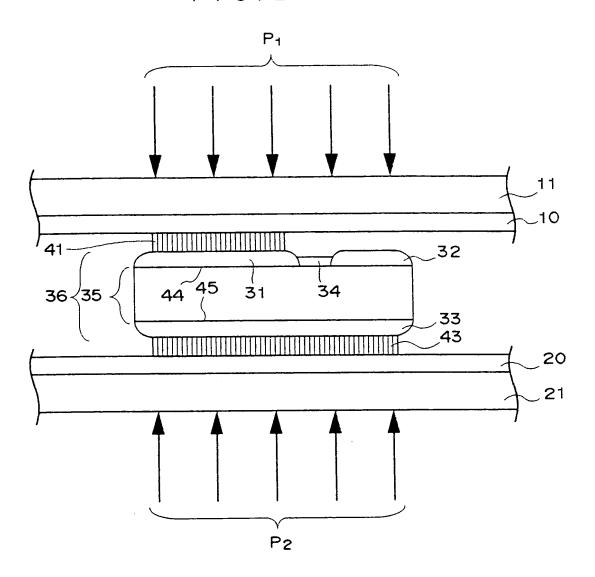
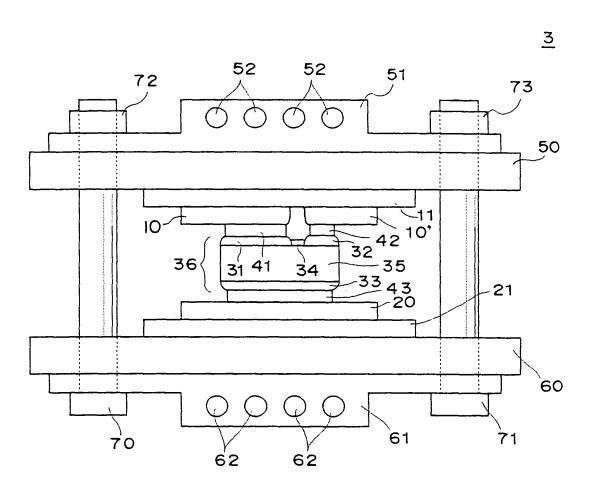
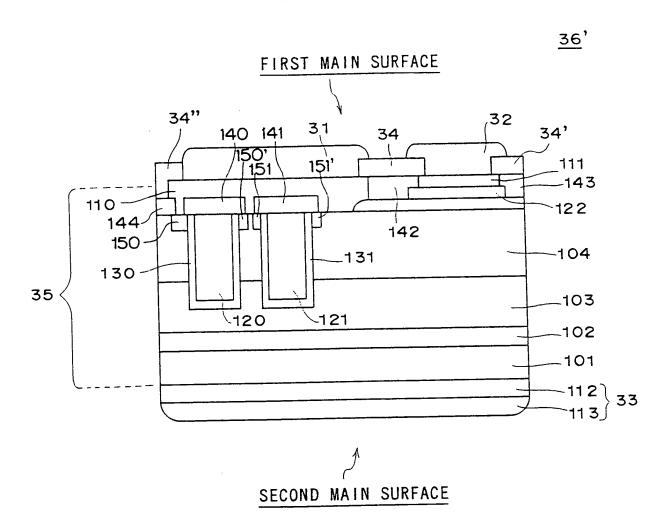


FIG. 3



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F1G.4



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MANUFACTURING PROCESS OF TRENCH IGBT ELEMENT

